

	3	(c22c021/.ipc. and (sc or scandium or si or silicon or ti or titanium or hf or hafnium) and ((grain or size) near2 ("mu.m" or "mu" or "mu." or micron or micrometer or ".mu.m" or ".mu." or "mum" or mu.m or \$1"mu.m")) and ((sputter\$4 or physical or vapor) near3 target)) not ((c22c021/.ipc. and (sc or scandium or si or silicon or ti or titanium or hf or hafnium) and (ecae or ((equal or channel) near2 (extrusion or extruded or extrude))) and ((grain or size) near2 ("mu.m" or "mu" or "mu." or micron or micrometer or ".mu.m" or ".mu." or "mum" or mu.m or \$1"mu.m")) and ((sputter\$4 or physical or vapor) near3 target)) ((148/437,415.ccls. or 420/548,552.ccls.) and (sc or scandium or si or silicon or ti or titanium or hf or hafnium) and (grain or size near2 ("mu.m" or "mu" or "mu." or micron or micrometer or ".mu.m" or ".mu." or "mum" or mu.m or \$1"mu.m")) and ((sputter\$4 or physical or vapor) near3 target)))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/20 17:09
	12	c22c021/.ipc. and (sc or scandium or si or silicon or ti or titanium or hf or hafnium) and ((grain or size) near2 ("mu.m" or "mu" or "mu." or micron or micrometer or ".mu.m" or ".mu." or "mum" or mu.m or \$1"mu.m")) and ((sputter\$4 or physical or vapor) near3 target)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/20 18:44
	2	5780755.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/20 17:16
	2	(sputter\$4 near2 target) and morillo.xa.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/20 17:16
	9	c22c021/.ipc. and (si or silicon) and ((grain or size) near2 ("mu.m" or "mu" or "mu." or micron or micrometer or ".mu.m" or ".mu." or "mum" or mu.m or \$1"mu.m")) and ((sputter\$4 or physical or vapor) near3 target)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/20 18:44
	22	(148/437,415.ccls. or 420/548,552.ccls.) and (si or silicon) and (grain or size near2 ("mu.m" or "mu" or "mu." or micron or micrometer or ".mu.m" or ".mu." or "mum" or mu.m or \$1"mu.m")) and ((sputter\$4 or physical or vapor) near3 target)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/20 18:45
	30	((al or aluminum) near2 (alloy or base or based or balance)) and (si or silicon) and ((grain or size) near2 ("mu.m" or "mu" or "mu." or micron or micrometer or ".mu.m" or ".mu." or "mum" or mu.m or \$1"mu.m")) and ((sputter\$4 or physical or vapor) near3 target) and (148/.ccls. or 420/.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/20 18:46
	46	(c22c021/.ipc. and (si or silicon) and ((grain or size) near2 ("mu.m" or "mu" or "mu." or micron or micrometer or ".mu.m" or ".mu." or "mum" or mu.m or \$1"mu.m")) and ((sputter\$4 or physical or vapor) near3 target)) ((148/437,415.ccls. or 420/548,552.ccls.) and (si or silicon) and (grain or size near2 ("mu.m" or "mu" or "mu." or micron or micrometer or ".mu.m" or ".mu." or "mum" or mu.m or \$1"mu.m")) and ((sputter\$4 or physical or vapor) near3 target)) ((al or aluminum) near2 (alloy or base or based or balance)) and (si or silicon) and ((grain or size) near2 ("mu.m" or "mu" or "mu." or micron or micrometer or ".mu.m" or ".mu." or "mum" or mu.m or \$1"mu.m")) and ((sputter\$4 or physical or vapor) near3 target)) ((al or aluminum) near2 (alloy or base or based or balance)) and (si or silicon) and ((grain or size) near2 ("mu.m" or "mu" or "mu." or micron or micrometer or ".mu.m" or ".mu." or "mum" or mu.m or \$1"mu.m")) and ((sputter\$4 or physical or vapor) near3 target)) and (148/.ccls. or 420/.ccls.))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/20 18:46
	15	(148/437,415.ccls. or 420/548,552.ccls.) and (sc or scandium or si or silicon or ti or titanium or hf or hafnium) and ((sputter\$4 or physical or vapor) near3 target) and (high near2 purity)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/20 18:54